

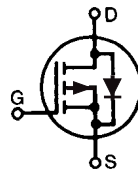
**TrenchP™**  
**Power MOSFET**
**IXTR120P20T**

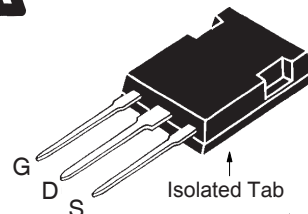
$$V_{DSS} = -200V$$

$$I_{D25} = -90A$$

$$R_{DS(on)} \leq 32m\Omega$$

$$t_{rr} \leq 300ns$$

 P-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Rectifier

 ISOPLUS247  

 E153432

 G = Gate      D = Drain  
 S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	- 200	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	- 200	V
$V_{GSS}$	Continuous	$\pm 15$	V
$V_{GSM}$	Transient	$\pm 25$	V
$I_{D25}$	$T_C = 25^\circ C$	- 90	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	- 400	A
$I_A$	$T_C = 25^\circ C$	-100	A
$E_{AS}$	$T_C = 25^\circ C$	3	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	10	V/ns
$P_D$	$T_C = 25^\circ C$	595	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$V_{ISOL}$	50/60 Hz, 1 Minute	2500	V~
$F_C$	Mounting Force	20..120/4.5..27	N/lb.
<b>Weight</b>		5	g

**Features**

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Rectifier
- Low  $R_{DS(ON)}$  and  $Q_G$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu A$	- 200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	- 2.5		V
$I_{GSS}$	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$			- 25 $\mu A$ - 300 $\mu A$
	$T_J = 125^\circ C$			
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = -60A$ , Note 1			32 m $\Omega$

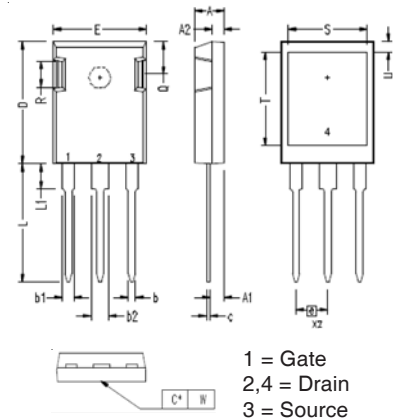
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = -10\text{V}$ , $I_D = -60\text{A}$ , Note 1	85	145	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = -25\text{V}$ , $f = 1\text{MHz}$		73	nF
$C_{oss}$			2550	pF
$C_{rss}$			480	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = -60\text{A}$ $R_G = 1\Omega$ (External)		90	ns
$t_r$			85	ns
$t_{d(off)}$			200	ns
$t_f$			50	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = -60\text{A}$		740	nC
$Q_{gs}$			220	nC
$Q_{gd}$			120	nC
$R_{thJC}$			0.21	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			-120 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			-480 A
$V_{SD}$	$I_F = -100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			-1.4 V
$t_{rr}$	$I_F = -60\text{A}$ , $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -100\text{V}$ , $V_{GS} = 0\text{V}$			300 ns
$Q_{RM}$			3.3	$\mu\text{C}$
$I_{RM}$			25.6	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### ISOPLUS247 (IXTR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.085	1.91	2.15
b2	.115	.126	2.92	3.20
C	.024	.033	0.61	0.83
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.811	19.81	20.60
L1	.150	.172	3.81	4.38
Q	.220	.244	5.59	6.20
R	.170	.191	4.32	4.85
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03
W	0	.004	0	0.10

### PRELIMINARY TECHNICAL INFORMATION

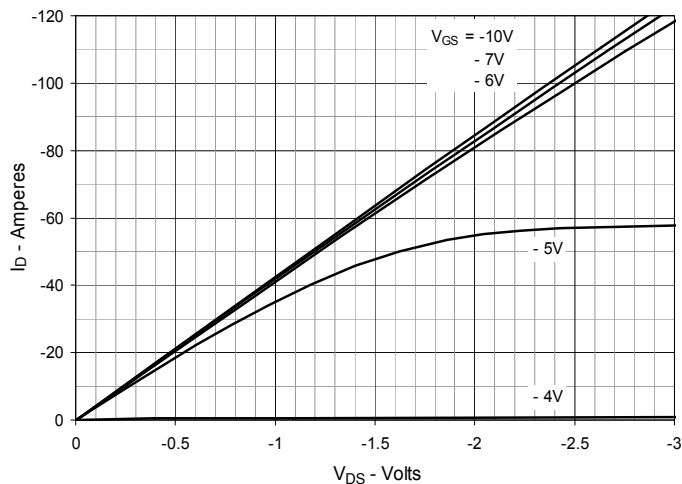
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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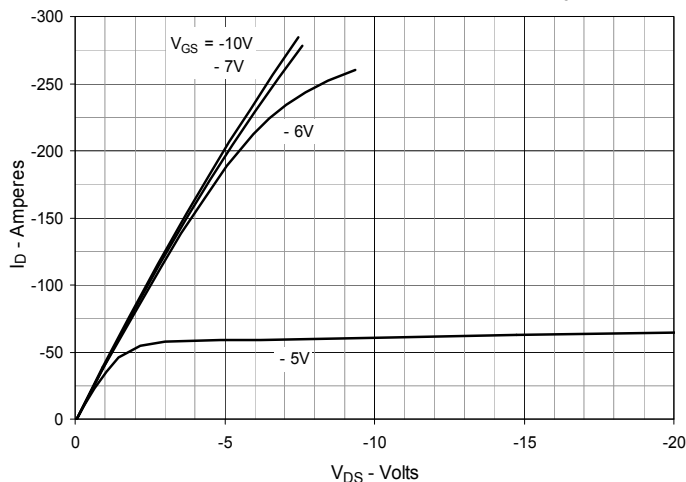
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

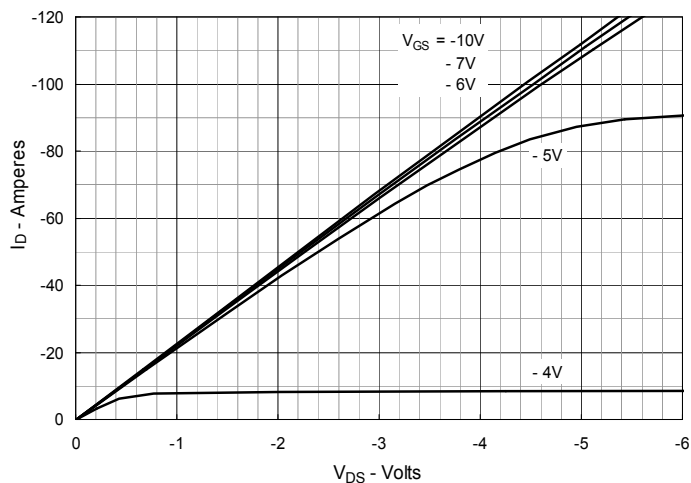
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



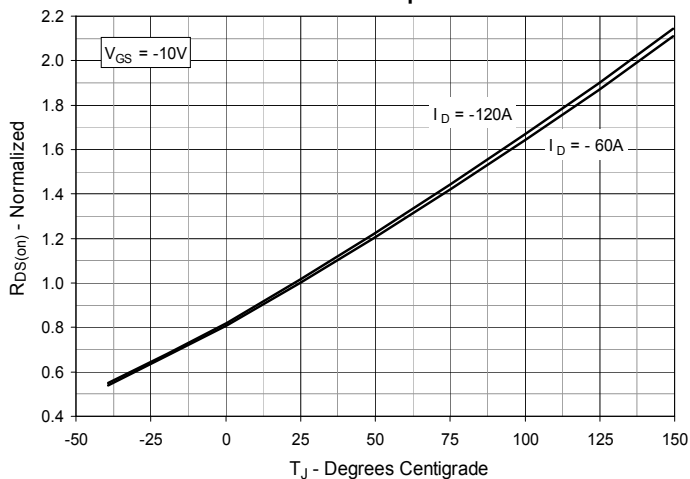
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



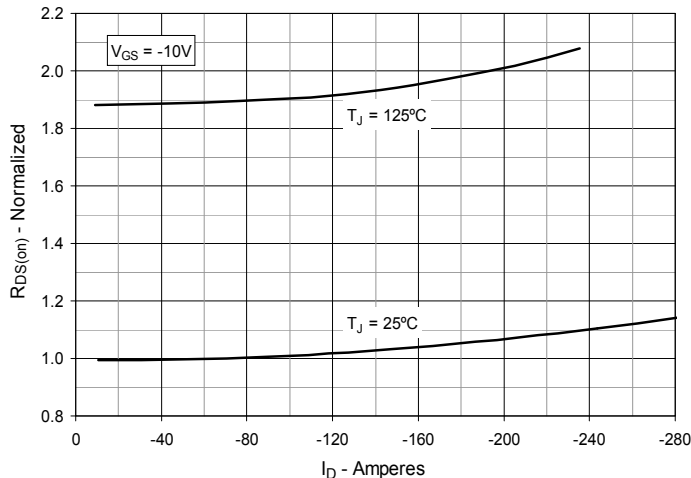
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



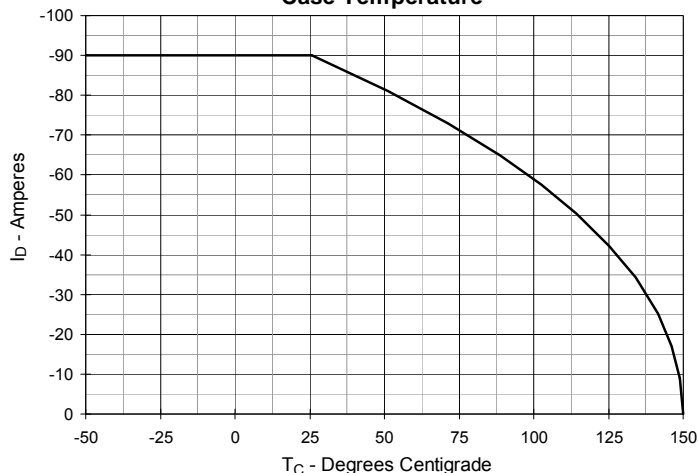
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -60\text{A}$  Value vs. Junction Temperature**



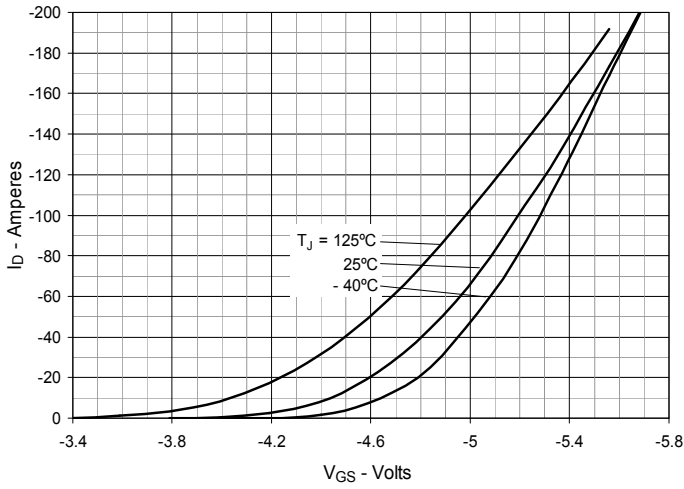
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -60\text{A}$  Value vs. Drain Current**



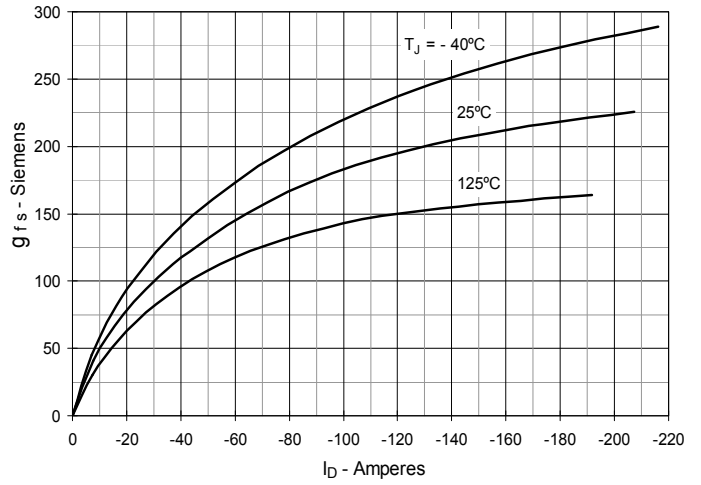
**Fig. 6. Maximum Drain Current vs. Case Temperature**



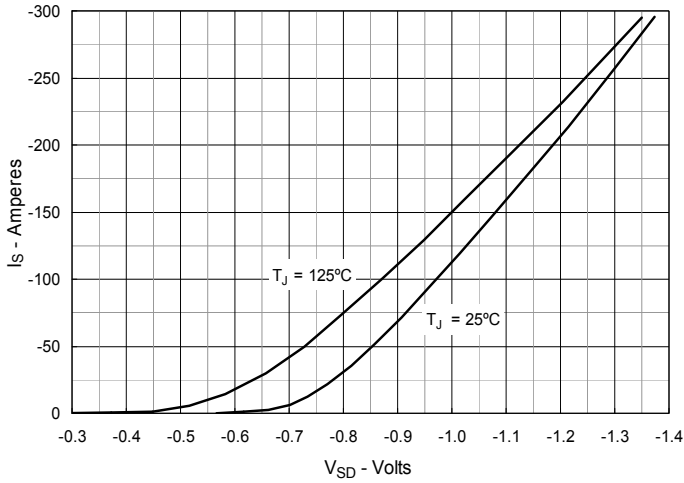
**Fig. 7. Input Admittance**



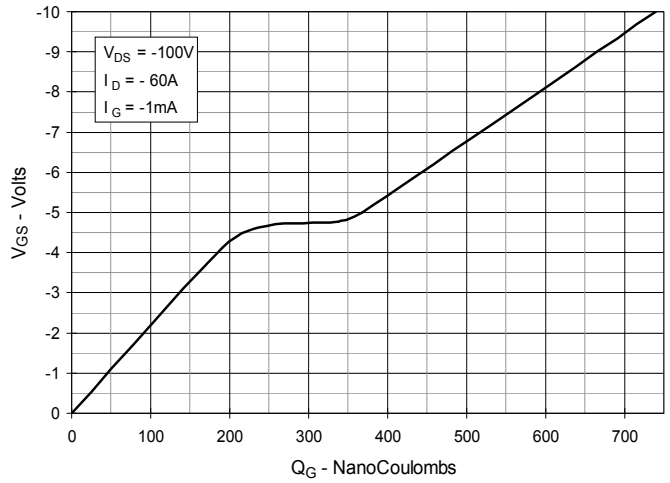
**Fig. 8. Transconductance**



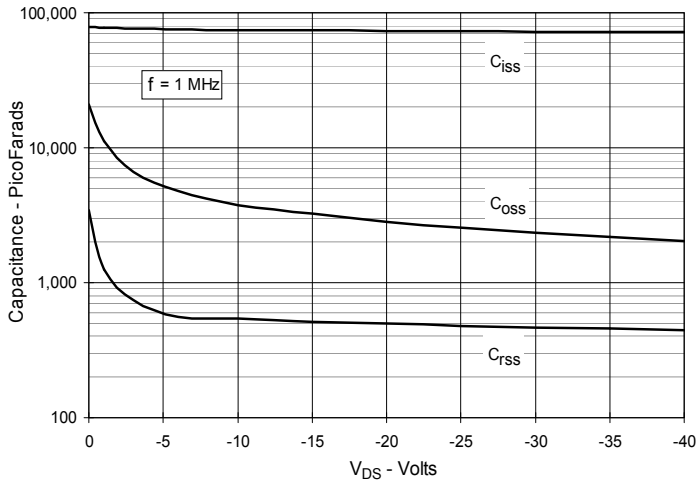
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



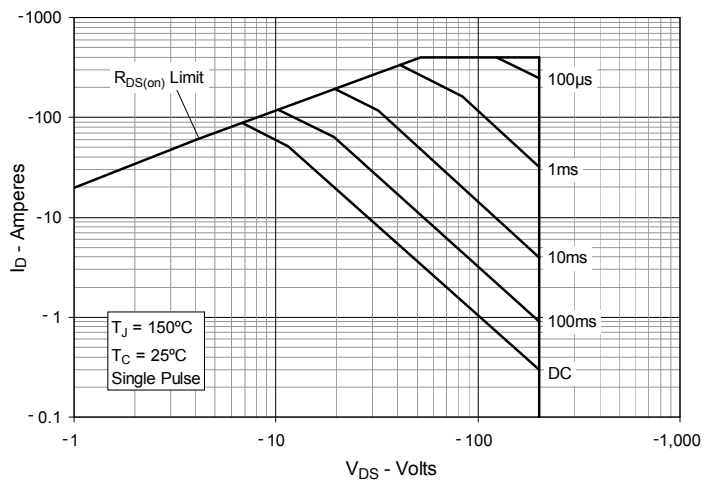
**Fig. 10. Gate Charge**



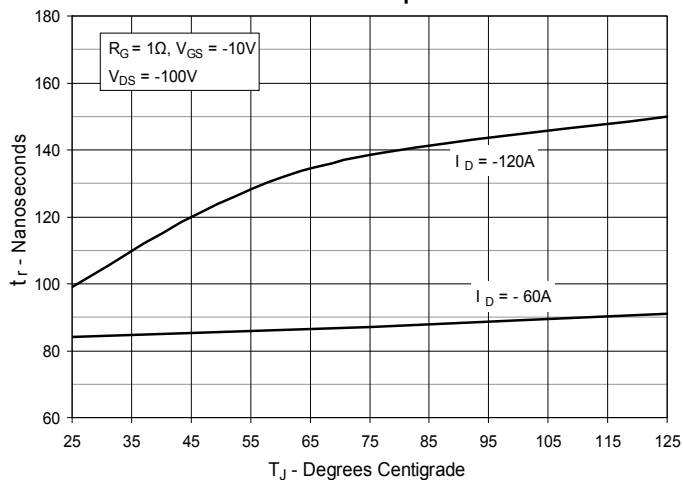
**Fig. 11. Capacitance**



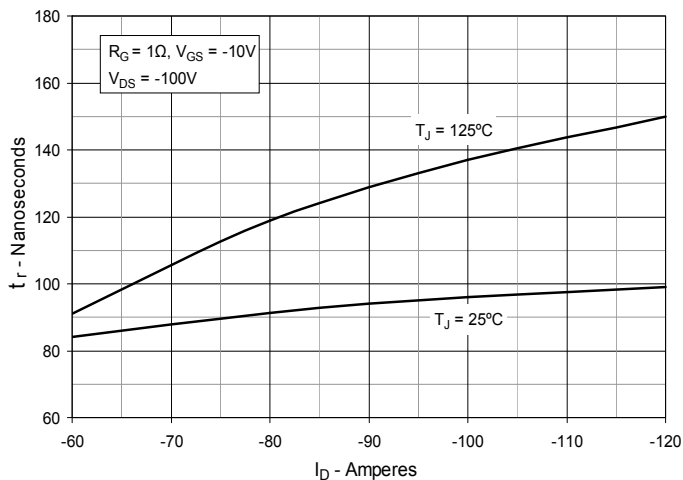
**Fig. 12. Forward-Bias Safe Operating Area**



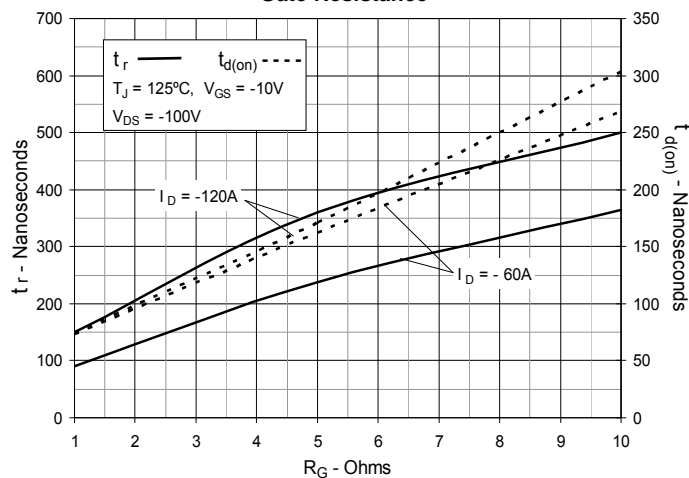
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



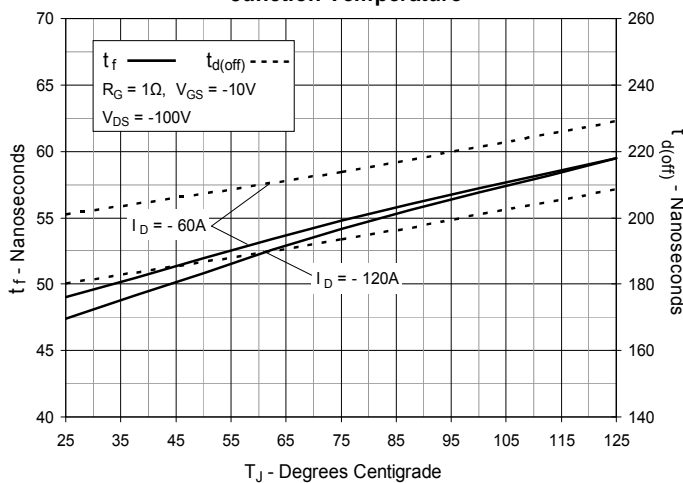
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



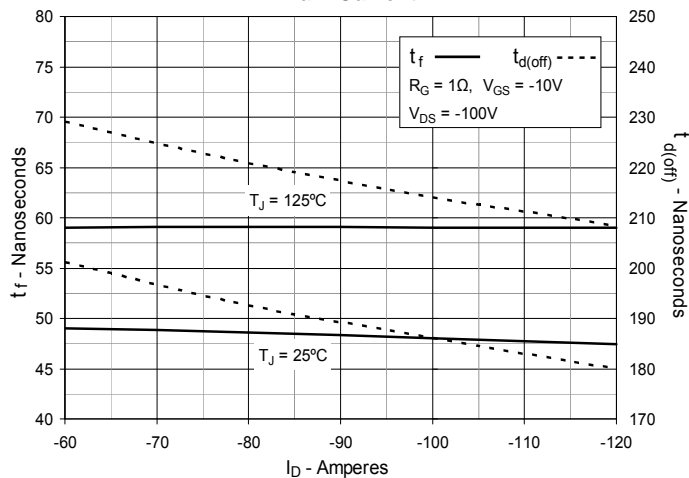
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

